

**VEER SURENDRA SAI UNIVERSITY OF TECHNOLOGY (VSSUT), ODISHA**  
**Odd Mid Semester Examination for Academic Session 2023-24**

COURSE NAME: B.Tech

SEMESTER: I<sup>st</sup>

BRANCH NAME: All Non circuit Branches (A,B,C,K,L,M,N)

SUBJECT NAME: **BASIC ELECTRONICS**

FULL MARKS: 30

TIME: 90 Minutes

Answer **All** Questions.

The figures in the right hand margin indicate Marks. *Symbols carry usual meaning.*

- Q1. Answer all Questions. [2 × 3]
- What is "Depletion region" in p-n junction? How it is formed? - CO1
  - What is the significance of the term field-effect in "FET"? - CO2
  - Explain the "Identity Law" of Boolean algebra. - CO3
- Q2. [8]CO1
- With neat circuit diagram explain the operation of bridge rectifier. [4]
  - The reverse saturation current of a Si diode at 27°C is 7μA. Determine the forward current that will flow in the diode when 0.65V is applied. [4]  

OR
  - Draw and explain the output characteristics of a PNP transistor in CE configuration. [4]
  - Mention different region of operation of BJT. How these can be achieved? Discuss applications of CB, CE and CC mode of BJT on the above regions. [4]
- Q3. [8]CO2
- Compare the construction and operation of n-channel JFET and n-channel D-MOSFET. [4]
  - Explain the operation of p-channel E-MOSFET with its characteristics. [4]
- OR
- Sketch the symbol and drain characteristic curve of p-channel JFET and n-channel E-MOSFET. [8]
  - Write the current expression ( $I_D$ ) for JFET, D-MOSFET and E-MOSFET.
  - For given  $I_{DSS} = 20\text{mA}$ ,  $V_p = -4\text{V}$ , find the drain current ( $I_D$ ), source current ( $I_S$ ) and gate current ( $I_G$ ) in a D-MOSFET for  $V_{GS} = -3\text{V}$ .  $I_G = \text{negligible}$
- Q4. [8]CO3
- Convert (i)  $(1AD.E)_{16}$  to decimal and octal equivalent. [4]  
(ii)  $(356.15)_8$  to binary and decimal equivalent.
  - Simplify the Boolean expression.  $Y = AB + \bar{A}C + \bar{A}\bar{B}(AB + C)$  [4]
- OR
- State and prove De Morgan's theorem for three variables. [4]
  - Subtract (i)  $(1111.101)_2$  from  $(1001.101)_2$  using 1's complement method. [4]  
(ii)  $(11101.111)_2$  from  $(11111.101)_2$  using 2's complement method.

$V_{GS}^2 = (I_{DSS} - I_D) R_{DS(on)}$

$$I_D = I_{DSS} \left( 1 - \frac{V_{GS}}{V_p} \right)^2$$